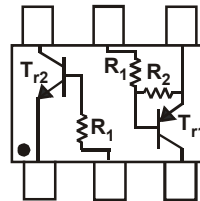
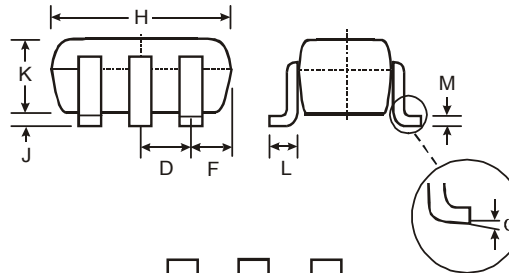
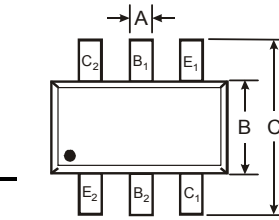


### Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- One 500mA PNP and One 100mA NPN
- Lead Free/RoHS Compliant (Note 1)
- "Green" Device (Note 3 and 4)

### Mechanical Data

- Case: SOT-363
- Case Material - Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020A
- Terminals: Finish - Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Code: C73 See Page 4
- Ordering & Date Code: See Page 4
- Terminal Connections: See Diagram
- Weight: 0.015 grams (approximate)



SCHEMATIC DIAGRAM

| SOT-363              |              |      |
|----------------------|--------------|------|
| Dim                  | Min          | Max  |
| A                    | 0.10         | 0.30 |
| B                    | 1.15         | 1.35 |
| C                    | 2.00         | 2.20 |
| D                    | 0.65 Nominal |      |
| F                    | 0.30         | 0.40 |
| H                    | 1.80         | 2.20 |
| J                    | —            | 0.10 |
| K                    | 0.90         | 1.00 |
| L                    | 0.25         | 0.40 |
| M                    | 0.10         | 0.25 |
| $\alpha$             | 0°           | 8°   |
| All Dimensions in mm |              |      |

| P/N     |     | R1   | R2  |
|---------|-----|------|-----|
| MIMD10A | Tr1 | 0.1K | 10K |
|         | Tr2 | 10K  | -   |

### Maximum Ratings PNP Section Tr1 @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic | Symbol          | Value    | Unit |
|----------------|-----------------|----------|------|
| Supply Voltage | V <sub>CC</sub> | -50      | V    |
| Input Voltage  | V <sub>IN</sub> | -5 to +5 | V    |
| Output Current | I <sub>O</sub>  | -500     | mA   |

### Maximum Ratings NPN Section Tr2 @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic            | Symbol           | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage    | V <sub>CBO</sub> | 50    | V    |
| Collector-Emitter Voltage | V <sub>CEO</sub> | 50    | V    |
| Emitter-Base Voltage      | V <sub>EBO</sub> | 5     | V    |
| Collector Current         | I <sub>C</sub>   | 100   | mA   |

### Maximum Ratings - Total @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                          | Symbol                            | Value       | Unit |
|-----------------------------------------|-----------------------------------|-------------|------|
| Power Dissipation (Note 2)              | P <sub>d</sub>                    | 200         | mW   |
| Operating and Storage Temperature Range | T <sub>j</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

- Notes:
1. No purposefully added lead.
  2. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.
  3. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

**Electrical Characteristics PNP Section Tr1** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic          | Symbol              | Min  | Typ  | Max  | Unit | Test Condition                                             |
|-------------------------|---------------------|------|------|------|------|------------------------------------------------------------|
| Input Voltage           | V <sub>I(off)</sub> | -0.3 | —    | —    | V    | V <sub>CC</sub> = -5V, I <sub>O</sub> = -100μA             |
|                         | V <sub>I(on)</sub>  | —    | —    | -1.5 |      | V <sub>O</sub> = 0.3, I <sub>O</sub> = -100mA              |
| Output Voltage          | V <sub>O(on)</sub>  | —    | -0.1 | -0.3 | V    | I <sub>O</sub> = -100mA/-5mA                               |
| Input Current           | I <sub>I</sub>      | —    | —    | -25  | mA   | V <sub>I</sub> = -2V                                       |
| Output Current          | I <sub>O(off)</sub> | —    | —    | -0.5 | μA   | V <sub>CC</sub> = -50V, V <sub>I</sub> = 0V                |
| DC Current Gain         | G <sub>I</sub>      | 68   | —    | —    | —    | —                                                          |
| Gain-Bandwidth Product* | f <sub>T</sub>      | —    | 200  | —    | MHz  | V <sub>CE</sub> = -10V, I <sub>E</sub> = -50mA, f = 100MHz |

\* Transistor - For Reference Only

**Electrical Characteristics NPN Section Tr2** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                       | Symbol               | Min | Typ | Max | Unit | Test Condition                                           |
|--------------------------------------|----------------------|-----|-----|-----|------|----------------------------------------------------------|
| Collector-Base Breakdown Voltage     | BV <sub>CBO</sub>    | 50  | —   | —   | V    | I <sub>C</sub> = 50μA                                    |
| Collector-Emitter Breakdown Voltage  | BV <sub>CEO</sub>    | 50  | —   | —   | V    | I <sub>C</sub> = 1mA                                     |
| Emitter-Base Breakdown Voltage       | BV <sub>EBO</sub>    | 5   | —   | —   | V    | I <sub>E</sub> = 50μA                                    |
| Collector Cutoff Current             | I <sub>CBO</sub>     | —   | —   | 0.5 | μA   | V <sub>CB</sub> = 50V                                    |
| Emitter Cutoff Current               | I <sub>EBO</sub>     | —   | —   | 0.5 | μA   | V <sub>EB</sub> = 4V                                     |
| Collector-Emitter Saturation Voltage | V <sub>CE(sat)</sub> | —   | —   | 0.3 | V    | I <sub>C</sub> /I <sub>B</sub> = 10mA / 1.0mA            |
| DC Current Transfer Ratio            | h <sub>FE</sub>      | 100 | 250 | 600 | —    | I <sub>C</sub> = 1mA, V <sub>CE</sub> = 5V               |
| Gain-Bandwidth Product*              | f <sub>T</sub>       | —   | 250 | —   | MHz  | V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA, f = 100MHz |

\* Transistor - For Reference Only

## Typical Curves – Tr2

NEW PRODUCT

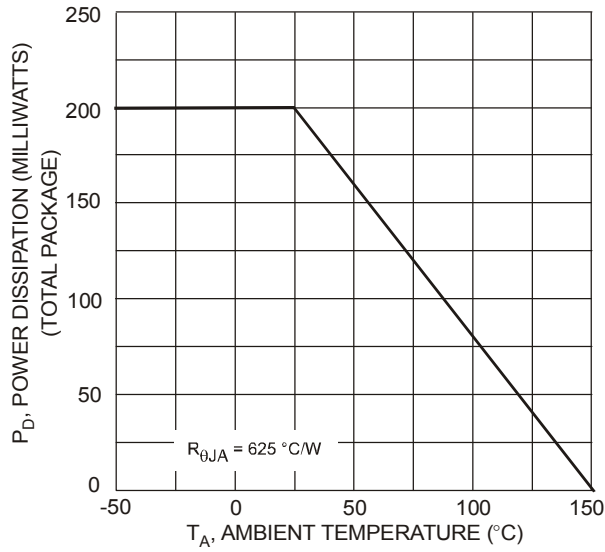


Fig. 1 Derating Curve

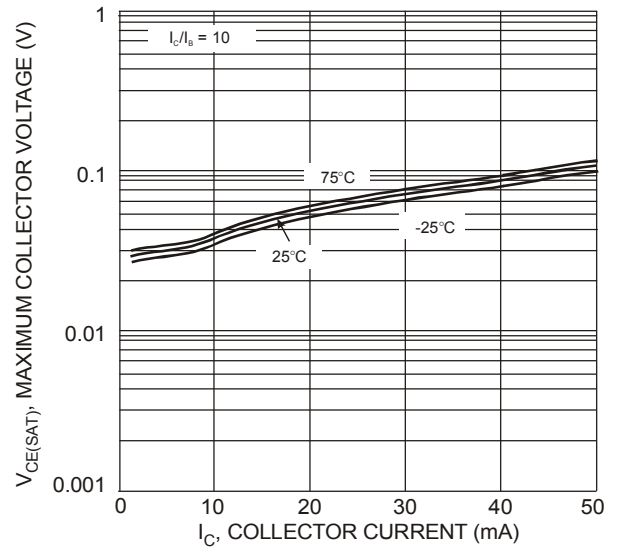


Fig. 2  $V_{CE(SAT)}$  vs.  $I_C$

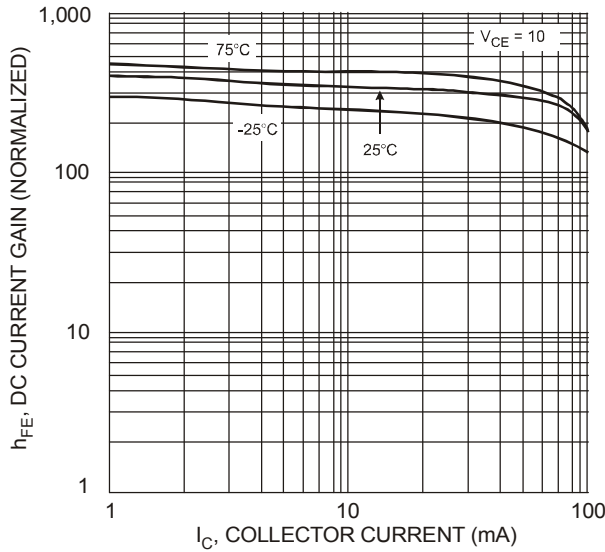


Fig. 3 DC Current Gain

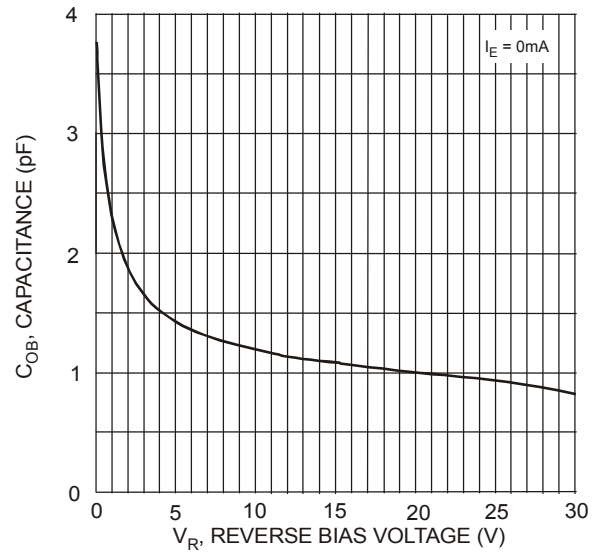


Fig. 4 Output Capacitance

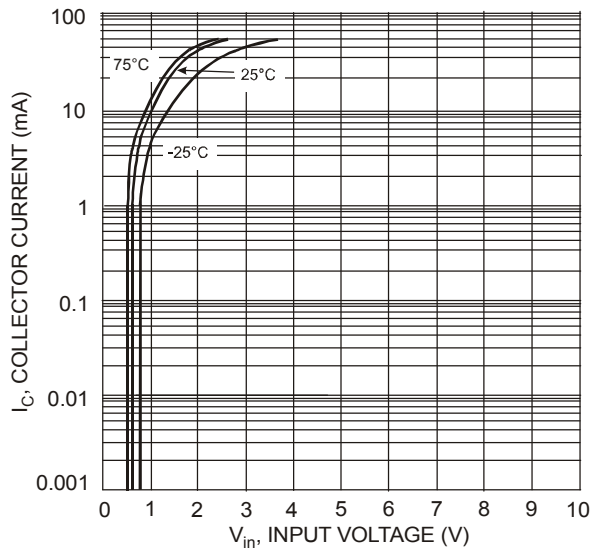


Fig. 5 Collector Current vs. Input Voltage

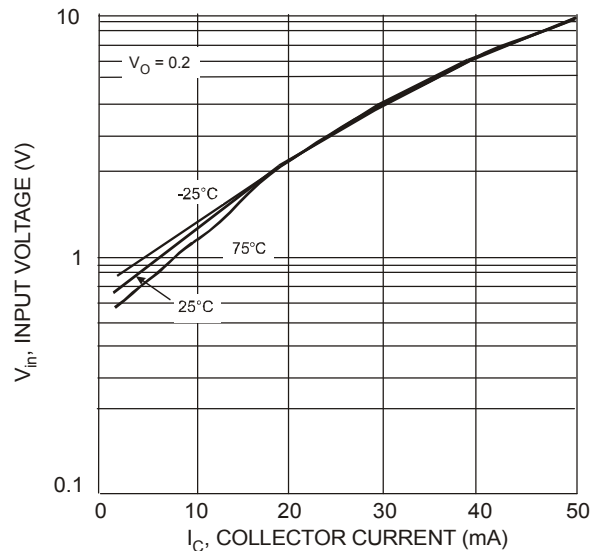


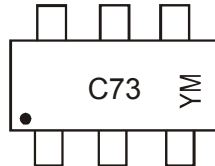
Fig. 6 Input Voltage vs. Collector Current

## Ordering Information (Note 5)

| Device      | Packaging | Shipping         |
|-------------|-----------|------------------|
| MIMD10A-7-F | SOT-363   | 3000/Tape & Reel |

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

## Marking Information



C73 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: P = 2003  
 M = Month ex: 9 = September

### Date Code Key

| Year | 2003 | 2004 | 2005 | 2006 | 2007 | 2008 | 2009 | 2010 | 2011 | 2012 |
|------|------|------|------|------|------|------|------|------|------|------|
| Code | P    | R    | S    | T    | U    | V    | W    | X    | Y    | Z    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

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- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

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- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: [org@lifeelectronics.ru](mailto:org@lifeelectronics.ru)

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